

WHAT IS CLAIMED IS:

1. An electro-optical device, comprising:
data lines extending in a first direction above a substrate;
scanning lines extending in a second direction, the scanning lines crossing
the data lines;
pixel electrodes and thin film transistors disposed so as to correspond to
regions in which the data lines and the scanning lines cross;
storage capacitors electrically connected to the thin film transistors and the
pixel electrodes; and
a shield layer disposed between the data lines and the pixel electrodes,
an upper electrode and a lower electrode between which a dielectric film
forming each storage capacitor being supported include a first portion laminated along a plane
parallel with one surface of the substrate and a second portion laminated along a plane that
intersects the surface of the substrate at an angle, whereby the sectional shape of the capacitor
includes a projecting shape.
2. The electro-optical device according to claim 1, the shield layer being
electrically connected to the upper electrode of each storage capacitor.
3. The electro-optical device according to claim 1, the projecting shape being
formed such that the lower electrode is formed so as to include a projecting portion from the
substrate.
4. The electro-optical device according to claim 3, the lower electrode being
formed of a light absorbing conductive material.
5. The electro-optical device according to claim 1, the projecting shape being
formed by forming a projecting member below the lower electrode.
6. The electro-optical device according to claim 1, the projecting shape
including a tapered shape.
7. The electro-optical device according to claim 1, the height of the projecting
shape being 50 to 1000 nm.
8. An electro-optical device according to claim 1,
the pixel electrodes being arranged in a matrix, and the scanning lines and
the data lines being formed in light shielding regions corresponding to the matrix; and
the storage capacitors being formed in the light shielding regions.
9. The electro-optical device according to claim 1, the projecting shape of each
storage capacitor being formed along at least one of each scanning line and each data line.

10. The electro-optical device according to claim 1, the dielectric film constituting each storage capacitor including a plurality of layers including different materials, and constituting a laminated body including one of the layers which comprises a material having a dielectric constant higher than those of the other layers.

11. The electro-optical device according to claim 10, the dielectric film including a silicon oxide film and a silicon nitride film.

12. The electro-optical device according to claim 1, further comprising:
as part of the laminated structure, an interlayer insulating film disposed as a base for each pixel electrode,
one surface of the interlayer insulating film being subjected to planarization processing.

13. An electro-optical device comprising:
data lines extending in a first direction above a substrate;
scanning lines extending in a second direction, the scanning lines crossing the data lines;
pixel electrodes and thin film transistors disposed so as to correspond to regions in which the data lines and the scanning lines cross;
storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and
a light shielding film disposed between each data line and each pixel electrode,
an upper electrode and a lower electrode between which a dielectric film forming each storage capacitor being supported include a first portion laminated along a plane parallel with one surface of the substrate and a second portion laminated along a plane that intersects the surface of the substrate at an angle, the sectional shape of the capacitor including a projecting shape.

14. An electronic apparatus including an electro-optical device comprising:
data lines extending in a first direction above a substrate;
scanning lines extending in a second direction, the scanning lines crossing the data lines;
pixel electrodes and thin film transistors disposed so as to correspond to regions in which the data lines and the scanning lines cross;
storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and

a shield layer disposed between the data lines and the pixel electrodes,
an upper electrode and a lower electrode between which a dielectric film
forming each storage capacitor being supported include a first portion laminated along a plane
parallel with one surface of the substrate and a second portion laminated along a plane that
intersects the surface of the substrate at an angle, the sectional shape of the capacitor
including a projecting shape.

15. A device according to claim 1, the second portion being laminated along a
plane substantially orthogonal to the surface of the substrate.

16. A device according to claim 13, the second portion being laminated along a
plane substantially orthogonal to the surface of the substrate.

17. A device according to claim 14, the second portion being laminated along a
plane substantially orthogonal to the surface of the substrate.

18. A device according to claim 1, the second portion being laminated along a
plane orthogonal to the surface of the substrate.

19. A device according to claim 13, the second portion being laminated along a
plane orthogonal to the surface of the substrate.

20. A device according to claim 14, the second portion being laminated along a
plane orthogonal to the surface of the substrate.